isc Silicon NPN RF Transistor 2SC2759

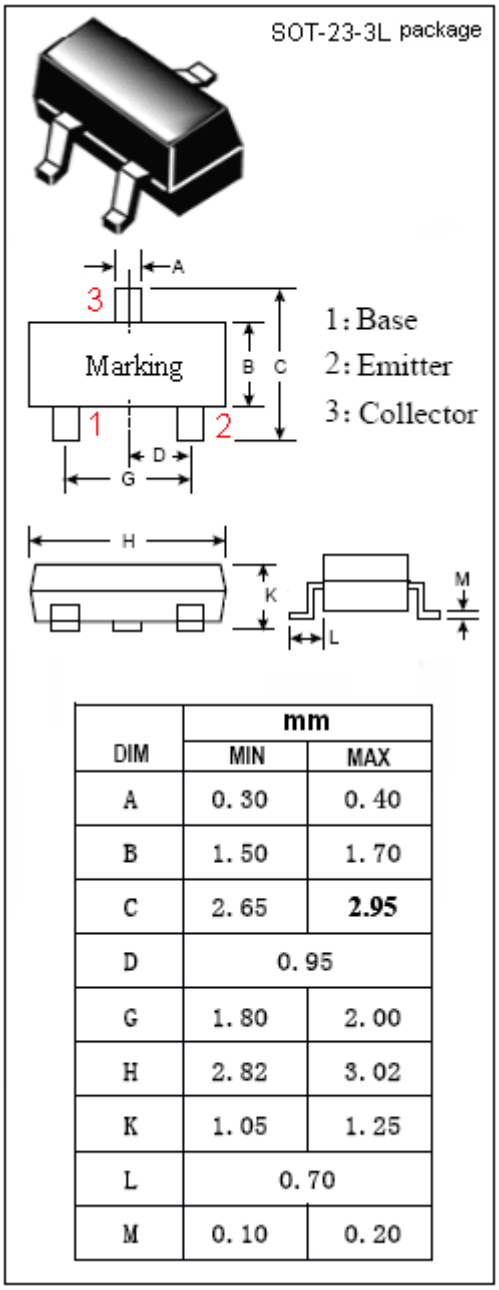
DESCRIPTION

- Low Noise
- High Conversion Gain

  G_{cb}= 12.5dB TYP. @I_E= -5mA, V_{CB}= 10V

APPLICATIONS

- Designed for use in VHF RF amplifier, local oscillator,mixer.



DIM	mm MIN	mm MAX
A	0.30	0.40
B	1.50	1.70
C	2.65	**2.95**
D	0.95	
G	1.80	2.00
H	2.82	3.02
K	1.05	1.25
L	0.70	
M	0.10	0.20

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	14	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current-Continuous	50	mA
P_C	Collector Power Dissipation @T_C=25℃	0.15	W
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature Range	-55~125	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CBO}	Collector Cutoff Current	V_{CB}= 15V; I_E= 0			0.1	μA
h_{FE}	DC Current Gain	I_C= 5mA ; V_{CE}= 10V	40		180	
f_T	Current-Gain—Bandwidth Product	I_C= 5mA ; V_{CE}= 10V	1.5	2.0		GHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V;f= 1.0MHz		1.0	1.3	pF
G_{cb}	Conversion Gain	I_E= -5mA ; V_{CB}= 10V; f= 900MHz; f_{OSC}= 935MHz, 115 dBμV	10	12.5		dB

◆ **h_{FE} Classification**

Marking	U21	U22	U23
h_{FE}	40-80	60-120	90-180